

# C3D04060E-Silicon Carbide Schottky Diode

# Z-REC<sup>TM</sup> RECTIFIER

 $\mathbf{V}_{\mathsf{RRM}} = 600 \ \mathsf{V}$ 

 $\mathbf{I}_{\mathsf{F}(\mathsf{AVG})} = 4 \; \mathsf{A}$ 

 $Q_{c} = 8.5 \text{ nC}$ 

#### **Features**

- 600-Volt Schottky Rectifier
- Optimized for PFC Boost Diode Application
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V<sub>F</sub>

# 1 2

**Package** 

TO-252-2

#### **Benefits**

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

# Applications

- Switch Mode Power Supplies
- Power Factor Correction
  - Typical PFC P<sub>out</sub>: 400W-600W



Part Number	Package	Marking
C3D04060E	TO-252-2	C3D04060

#### **Maximum Ratings**

Symbol	Parameter	Value	Unit	Test Conditions	Note
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	600	V		
$V_{\scriptscriptstyle{RSM}}$	Surge Peak Reverse Voltage	600	V		
V <sub>DC</sub>	DC Blocking Voltage	600	V		
$I_{\text{F(AVG)}}$	Average Forward Current	4	А	T <sub>c</sub> <160°C	
$I_{FRM}$	Repetitive Peak Forward Surge Current	22 17	А	$T_c$ =25°C, $t_p$ =10 mS, Half Sine Wave D=0.3 $T_c$ =110°C, $t_p$ =10 mS, Half Sine Wave D=0.3	
$\boldsymbol{I}_{\text{FSM}}$	Non-Repetitive Peak Forward Surge Current	31.9 28.5	А	$T_c$ =25°C, $t_p$ =10 mS, Half Sine Wave D=0.3 $T_c$ =110°C, $t_p$ =10 mS, Half Sine Wave D=0.3	
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	110	А	$T_c$ =25°C, $t_p$ =10 $\mu$ S, Pulse	
P <sub>tot</sub>	Power Dissipation	75 32.5	W	T <sub>c</sub> =25°C T <sub>c</sub> =110°C	
$T_{_{\mathrm{J}}}$ , $T_{_{\mathrm{stg}}}$	Operating Junction and Storage Temperature	-55 to +175	°C		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	



#### **Electrical Characteristics**

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V <sub>F</sub>	Forward Voltage	1.5 1.8	1.7 2.4	V	$I_F = 4 \text{ A } T_J = 25^{\circ}\text{C}$ $I_F = 4 \text{ A } T_J = 175^{\circ}\text{C}$	
$I_R$	Reverse Current	10 20	50 100	μA	$V_R = 600 \text{ V } T_J = 25^{\circ}\text{C}$ $V_R = 600 \text{ V } T_J = 175^{\circ}\text{C}$	
Q <sub>c</sub>	Total Capacitive Charge	8.5		nC	$V_R = 600 \text{ V, } I_F = 4A$ $di/dt = 500 \text{ A/}\mu\text{s}$ $T_J = 25^{\circ}\text{C}$	
С	Total Capacitance	251 22 21		pF	$V_R = 0 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 200 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 400 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$	

#### Note:

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Unit
$R_{_{ heta JC}}$	TO-252 Package Thermal Resistance from Junction to Case	2.02	°C/W

## **Typical Performance**

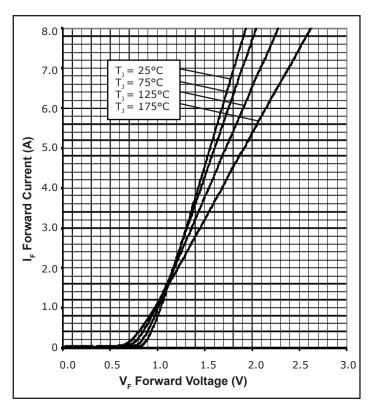


Figure 1. Forward Characteristics

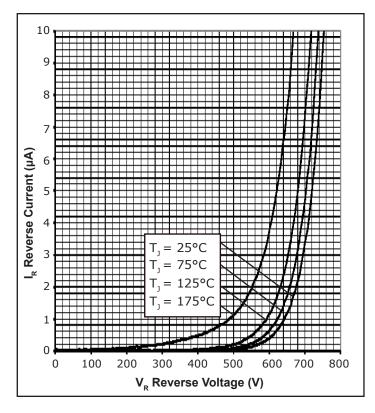
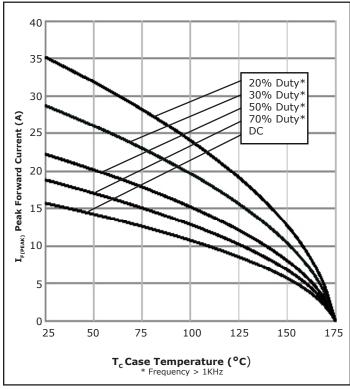


Figure 2. Reverse Characteristics

<sup>1.</sup> This is a majority carrier diode, so there is no reverse recovery charge.



## **Typical Performance**



\* Frequency > 1KHz \* /

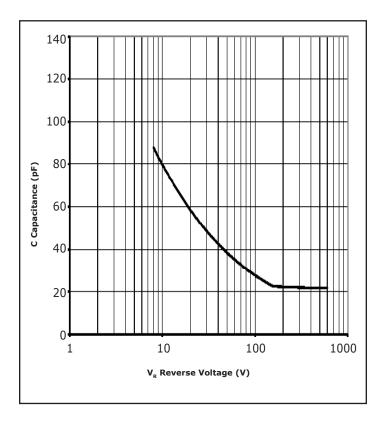


Figure 4. Capacitance vs. Reverse Voltage

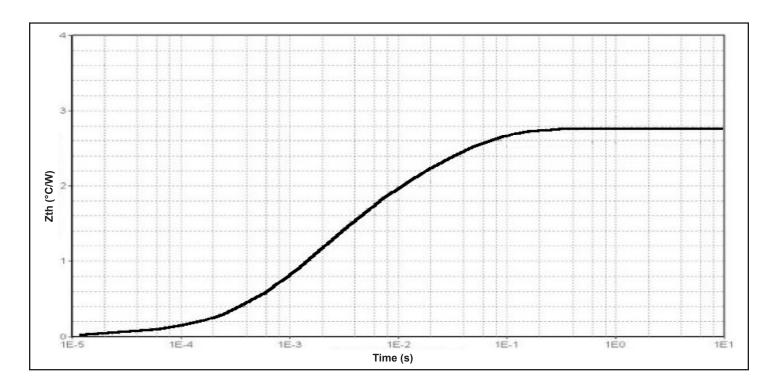


Figure 5. Transient Thermal Impedance



## **Typical Performance**

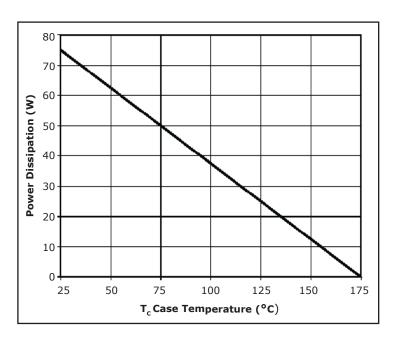
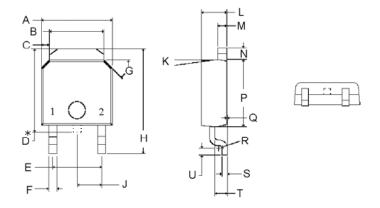


Figure 6. Power Derating



## **Package Dimensions**

Package TO-252-2





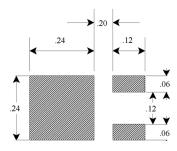
POS	Inc	hes	Millimeters		
PUS	Min	Max	Min	Max	
Α	.250	.289	6.350	7.341	
В	.197	.215	5.004	5.461	
С	.027	.050	.686	1.270	
D*	.270	.322	6.858	8.179	
Е	.178	.182	4.521	4.623	
F	.025	.045	.635	1.143	
G	44°	46°	44°	46°	
Н	.380	.410	9.652	10.414	
J	.090 TYP		2.286 TYP		
K	6°	8°	6°	8°	
L	.086	.094	2.184	2.388	
М	.018	.034	.457	.864	
N	.035	.050	.889	1.270	
Р	.231	.246	5.867	6.248	
Q	0.00	.005	0.00	.127	
R	R0.010 TYP		R0.25	4 TYP	
S	.017	.023	.432	.584	
Т	.038	.045	.965	1.143	
U	.021	.029	.533	.737	

#### Note:

<sup>\*</sup> Tab "D" may not be present



#### **Recommended Solder Pad Layout**



TO-252-2

Part Number	Package	Marking
C3D04060E	TO-252-2	C3D04060

#### **Diode Model**

$$\begin{array}{c|c} - & & \\ \hline V_T & & R_T \\ \end{array}$$

$$Vf_T = V_T + If * R_T$$

$$V_T = 0.98 + (T_J^* -1.8^*10^{-3})$$
  
 $R_T = 0.10 + (T_J^* 9.16^*10^{-4})$ 

Note: T<sub>i</sub> = Diode Junction Temperature In Degrees Celcius

"The levels of environmentally sensitive, persistent biologically toxic (PBT), persistent organic pollutants (POP), or otherwise restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2002/95/EC on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS), as amended through April 21, 2006.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, air traffic control systems, or weapons systems.

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